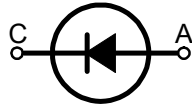
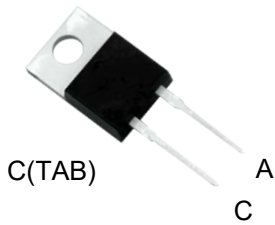
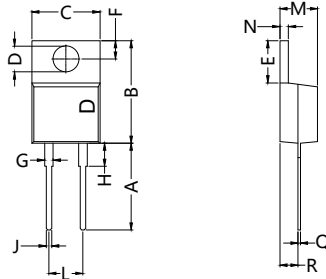


HUR2960

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes



Dimensions TO-220AC



Dim.	Millimeter	
	Min.	Max.
A	12.70	13.97
B	14.73	16.00
C	9.91	10.66
ØD	3.54	4.08
E	5.85	6.85
F	2.54	3.18
G	1.15	1.65
H	2.79	5.84
J	0.64	1.01
L	5.05BSC	
M	4.32	4.82
N	1.14	1.39
Q	0.35	0.56
R	2.29	2.79

A=Anode, C=Cathode, TAB=Cathode

	V_{RSM} V	V_{RRM} V
HUR2960	600	600

Symbol	Test Conditions	Maximum Ratings	Unit
I_{FRMS}	$T_C=135^\circ\text{C}$; rectangular, $d=0.5$	35	A
I_{FAVM}		30	
I_{FSM}	$T_{VJ}=45^\circ\text{C}$; $t_p=10\text{ms}$ (50Hz), sine	250	A
EAS	$T_{VJ}=25^\circ\text{C}$; non-repetitive; $I_{AS}=1.3\text{A}$; $L=180\mu\text{H}$	0.2	mJ
I_{AR}	$V_A=1.5 \cdot V_R$ typ.; $f=10\text{kHz}$; repetitive	0.1	A
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	
T_{stg}		-55...+150	
P_{tot}	$T_C=25^\circ\text{C}$	165	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Sirectifier®

HUR2960

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I _R	T _{VJ} =25°C; V _R =V _{RRM}		250	uA
	T _{VJ} =150°C; V _R =V _{RRM}		1	mA
V _F	I _F =30A; T _{VJ} =150°C		1.26	V
	T _{VJ} =25°C		1.61	
R _{thJC} R _{thCH}		0.5	0.9	K/W
t _{rr}	I _F =1A; -di/dt=200A/us; V _R =30V; T _{VJ} =25°C	35		ns
I _{RM}	V _R =100V; I _F =50A; -di _F /dt=100A/us; T _{VJ} =100°C	6		A

FEATURES

- * International standard package
- * Planar passivated chips
- * Very short recovery time
- * Extremely low switching losses
- * Low I_{RM}-values
- * Soft recovery behaviour
- * RoHS compliant

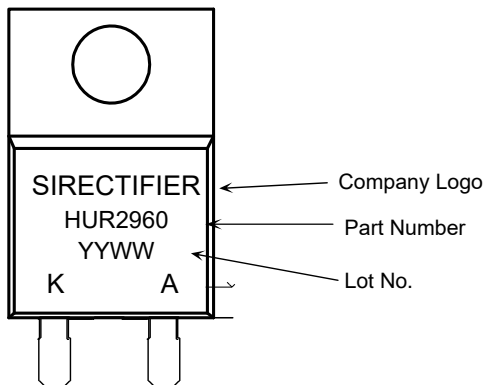
APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Antisaturation diode
- * Snubber diode
- * Free wheeling diode in converters and motor control circuits
- * Rectifiers in switch mode power supplies (SMPS)
- * Inductive heating
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * Avalanche voltage rated for reliable operation
- * Soft reverse recovery for low EMI/RFI
- * Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Marking



Ordering Information

Part Number	Package	Shipping	Marking Code
HUR2960	TO-220AC	50pcs / Tube	HUR2960

Sirectifier®

HUR2960

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

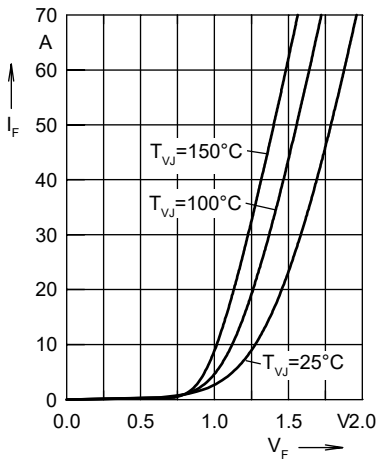


Fig. 1 Forward current I_F versus V_F

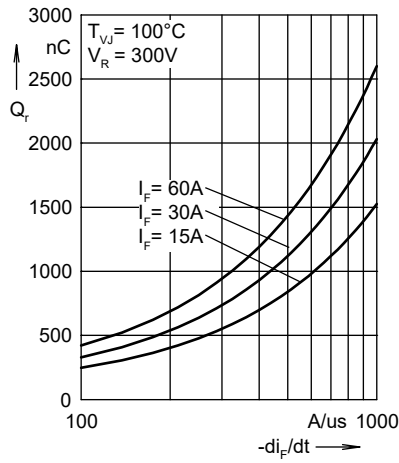


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

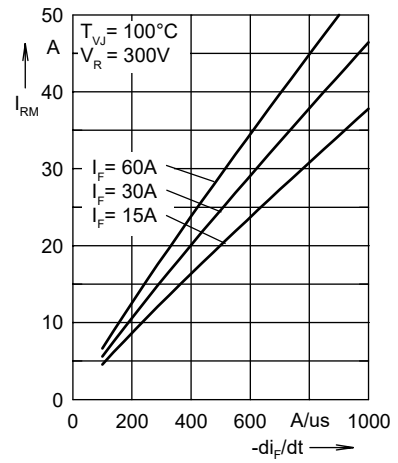


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

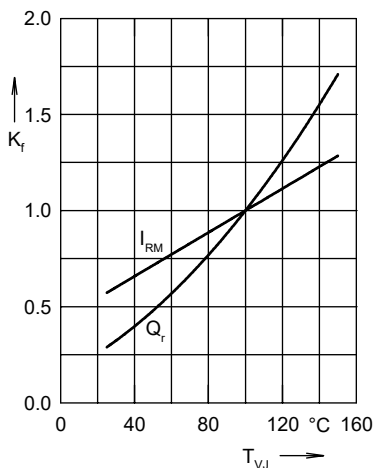


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

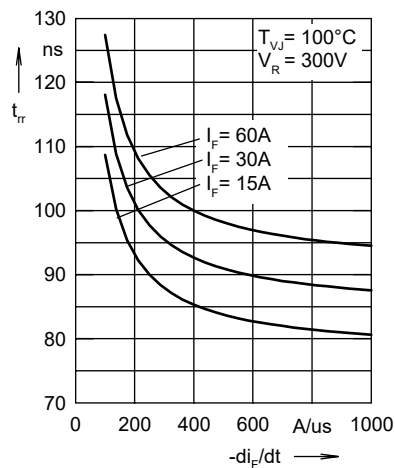


Fig. 5 Recovery time t_{tr} versus $-di_F/dt$

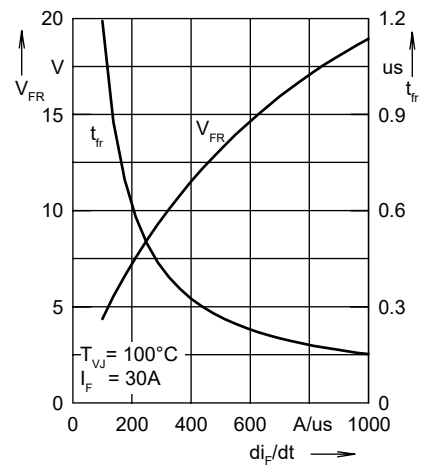


Fig. 6 Peak forward voltage V_{FR} and t_{tr} versus di_F/dt

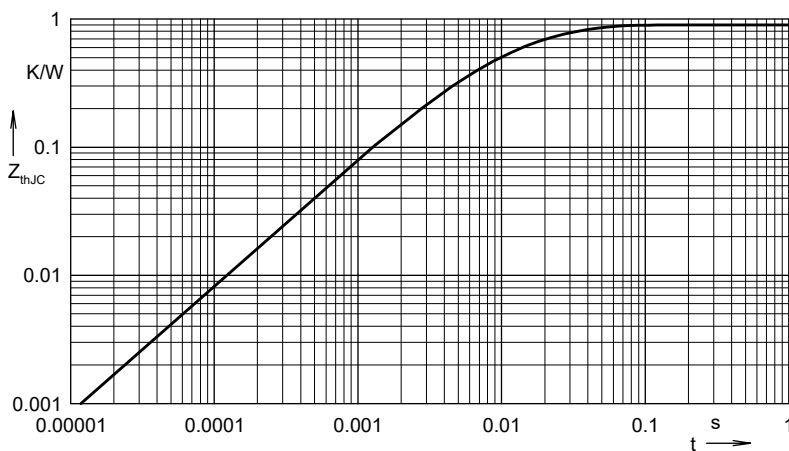


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162